

Title (en)

[100] OR [110] ALIGNED, SEMICONDUCTOR-BASED, LARGE-AREA, FLEXIBLE, ELECTRONIC DEVICES

Title (de)

AUSGERICHTETE AUF HALBLEITERN BASIERENDE GROSSFLÄCHIGE FLEXIBLE ELEKTRONISCHE ANORDNUNGEN

Title (fr)

DISPOSITIFS ÉLECTRONIQUES FLEXIBLES DE GRANDE SURFACE, BASÉS SUR DES SEMI-CONDUCTEURS, DE TEXTURE [100] OU [110] ET ALIGNÉS

Publication

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Application

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Priority

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Abstract (en)

[origin: WO2009096932A1] Novel articles and methods to fabricate the same resulting in flexible, large-area, [100] or [110] textured, semiconductor-based, electronic devices are disclosed. Potential applications of resulting articles are in areas of photovoltaic devices, flat-panel displays, thermophotovoltaic devices, ferroelectric devices, light emitting diode devices,, computer hard disc drive devices, magnetoresistance based devices, photoluminescence based devices, non-volatile memory devices, dielectric devices, thermoelectric devices and quantum dot laser devices.

IPC 8 full level

H01L 31/0368 (2006.01); **H01L 21/02** (2006.01); **H01L 21/20** (2006.01); **H01L 29/06** (2006.01); **H01L 29/12** (2006.01); **H01L 29/786** (2006.01); **H01L 31/032** (2006.01); **H01L 31/0392** (2006.01); **H01L 31/0687** (2012.01); **H01L 31/18** (2006.01)

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B82Y 10/00 (2013.01); **H01L 21/02425** (2013.01); **H01L 21/02433** (2013.01); **H01L 21/02439** (2013.01); **H01L 21/02488** (2013.01); **H01L 21/02521** (2013.01); **H01L 21/02609** (2013.01); **H01L 29/0665** (2013.01); **H01L 29/0673** (2013.01); **H01L 29/127** (2013.01); **H01L 29/78603** (2013.01); **H01L 31/0368** (2013.01); **H01L 31/0687** (2013.01); **H01L 31/182** (2013.01); **H01L 21/02532** (2013.01); **H01L 21/02568** (2013.01); **H01L 29/78651** (2013.01); **H01L 29/78681** (2013.01); **H01L 29/7869** (2013.01); **Y02E 10/544** (2013.01); **Y02E 10/546** (2013.01); **Y02P 70/50** (2015.11)

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